

Please replace the abstract with the following amended abstract:

**METHOD FOR FILLING A CONTACT HOLE AND
INTEGRATED CIRCUIT ARRANGEMENT WITH CONTACT HOLE**

An explanation is given of a method in which a base layer (50) is deposited in a contact hole region (30) under a protective gas, where base layer contains a nitride as main constituent. After the deposition of the base layer (50), a covering layer (54) is deposited under gaseous nitrogen. An adhesion promoting layer (32) results which is simple to produce and has good electrical properties.

(Figure 4)

A clean copy of the amended abstract appears in an attached sheet.